R01DS0186EJ0120 Rev.01.20 Sep 10, 2012

1. Overview

The SH7459 Group is a single-chip RISC (reduced instruction set computer) microcontroller based on a Renesas original RISC CPU core.

Basically the SH7459 Group is the same as the SH7456 Group. Please refer to SH7455 Group, SH7456 Group User's Manual: Hardware Rev.1.10 (Sep 22, 2011). Table 1.1 shows the differences between the SH7456 Group and the SH7459 Group.

* Henceforth, the bold letter portion (shaped portion) shows a difference from SH7456 Group.

Table 1.1 Products

Group	Product	Model	CPU Frequency	Memory Capacity	Package	FlexRay	Operating temperature (Ta)
SH7459	SH74593	R5F74593LBG	240 MHz	ROM: 1.5 Mbytes	PRBG0176GA-A	Yes	-40 to + 105 °C
				IL memory: 8 Kbytes,			
				OL memory: 16 Kbytes, and			
				SHwyRAM: 512 Kbytes			
SH7455	SH74552	R5F74552KBG	160MHz	ROM: 1Mbyte		Yes	-40 to +125°C
SH7456	SH74562	R5F74562KBG		IL memory: 8 Kbytes,		No	
SH7457	SH74572	R5F74572LBG	240MHz	OL memory: 16 Kbytes, and		Yes	-40 to +105°C
				SHwyRAM: 256 Kbytes			

2. Details

This section shows the details of the difference from SH7455 Group, SH7456 Group User's Manual: Hardware Rev.1.10 (Sep 22, 2011). Table 2.1 shows the difference between the SH74562 and the SH74593.

Table 2.1 Difference between SH74562 and SH74593

Page	Description
1-1	1.1 Features
	Product SuperHyway RAM (SHwyRAM) Capacity
	SH74562 256 Kbytes
	SH74593 512 Kbytes
1-4	Table 1.1 Specifications Overview: Descriptions of ROM
	Product ROM Capacity
	SH74562 1-Mbytes
	SH74593 1.5-Mbytes
	Table 1.1 Specifications Overview: Descriptions of RAM
	Product RAM Capacity
	SH74562 256-Kbytes
	SH74593 512-Kbytes
1-4	Table 1.1 Specifications Overview: Descriptions of CPG
	Product CPU clock (lck)
	SH74562 160 MHz maximum
	SH74593 240 MHz maximum



-	Description									
1-6	 Table 1.1 Specifications Overview: Descriptions of FlexRay 									
	Product Channels of FlexRay									
	SH74562 None: SH7456 Group									
	SH74593 Two channels: SH7459 Group									
1-7	Table 1.1 Specifications Overview: Descriptions of Operating temperature									
	Product Operating temperature									
	SH74562 Ta = -40° C to $+125^{\circ}$ C									
	SH74593 Ta = -40°C to + 105 °C									
Page 1-6 1-7 1-7 1-7 1-8 1-9 1-15 11-2 11-3	Table 1.2 Products									
	Product Model ROM Capacity SHwyRAM Capacity FlexRay									
	SH74562 R5F74562KBG 1 Mbyte 256 Kbytes No									
	SH74593 R5F74593LBG 1.5 Mbytes 512 Kbytes Yes									
	Please refer to Appendix A.									
1-8	Figure 1.1 Block Diagram									
	Product SH-4A core clock ROM Capacity SHwyRAM Capacity									
	SH74562 SH-4A core (160 MHz maximum) ROM (1 Mbyte) SHwyRAM (256 Kbytes)									
	SH74593 SH-4A core (240 MHz maximum) ROM (1.5 Mbytes) SHwyRAM (512 Kbytes)									
-	Figure 1.2 Pin Arrangement (Top Transparent View)									
1-15	Table 1.3 Pin Functions of pin A6									
	Product A6 pin									
	SH74562 Vcc									
	SH74593 Vss									
	Please refer to Appendix B.									
11-2	• Figure 11.2 Address Space (P0/U0 Area): Descriptions of 29-bit physical address space (Single chip)									
	Product ROM Capacity (Start address - Last address) SHwyRAM Capacity (Start address - Last address)									
	SH74562 1 Mbyte (H'0000 0000 – H'000F FFFF) 256 Kbytes(H'1800 0000 – H'1803 FFFF)									
	SH74593 1.5 Mbytes (H'0000 0000 – H'0017 FFFF) 512 Kbytes(H'1800 0000 – H'1807 FFFF)									
	Please refer to Appendix C.1.									
11-3	Figure 11.3 Address Space (P1 Area): Descriptions of 29-bit physical address space (Single chip)									
	Product ROM Capacity (Start address – Last address) SHwyRAM Capacity (Start address – Last address)									
	SH74562 1 Mbyte (H'8000 0000 – H'800F FFFF) 256 Kbytes(H'9800 0000 – H'9803 FFFF)									
	SH74593 1.5 Mbytes (H'8000 0000 – H'8017 FFFF) 512 Kbytes (H'9800 0000 – H'9807 FFFF)									
	Please refer to Appendix C.2.									
11-4	Figure 11.4 Address Space (P2 Area): Descriptions of 29-bit physical address space (Single chip)									
	Product ROM Capacity (Start address – Last address) SHwyRAM Capacity (Start address – Last address)									
	SH74562 1 Mbyte (H'A000 0000 – H'A00F FFFF) 256 Kbytes(H'B800 0000 – H'B803 FFFF)									
	SH74593 1.5 Mbytes (H'A000 0000 – H'A017 FFFF) 512 Kbytes(H'B800 0000 – H'B807 FFFF)									
	Please refer to Appendix C.3.									
11-5	• Figure 11.5 Address Space (P3 Area): Descriptions of 29-bit physical address space (Single chip)									
	Product ROM Capacity (Start address – Last address) SHwyRAM Capacity (Start address – Last address)									
	SH74562 1 Mbyte (H'C000 0000 – H'C00F FFFF) 256 Kbytes(H'D800 0000 – H'D803 FFFF)									
	SH74593 1.5 Mbytes (H'C000 0000 – H'C017 FFFF) 512 Kbytes(H'D800 0000 – H'D807 FFFF)									
	Please refer to Appendix C.4.									

Please refer to Appendix C.4.

Page	Descriptio	on									
12-1	• 12. RC	DM									
	Product	ROM Capacity									
	SH74562	1 Mbyte									
	SH74593	1.5 Mbytes									
	• 12.1 O	verview									
	Product	Area									
	SH74562	When the user boot MAT is selected,	the area from H'0000 8000 to H'000F FFFF has								
		an undefined value when read and bo	th writing and erasing are disabled.								
	SH74593	When the user boot MAT is selected,	the area from H'0000 8000 to H'0017 FFFF has								
		an undefined value when read and bo	th writing and erasing are disabled.								
	Figure	12.1 Memory MAT Configuration in ROI	M: Descriptions of User MAT								
	Product	Read : Start address – Last address	Program/erase : Start address – Last address								
	SH74562	H'0000 0000 – H'000F FFFF	H'FD80 0000 – H'FD8F FFFF								
	SH74593	SH74593 H'0000 0000 – H'0017 FFFF H'FD80 0000 – H'FD97 FFFF									
	Please ref	er to Appendix D.1.									



Page	Descriptio	n	
12-1	• 12.1 Ov	verview	
12-2	• Figure	12.2 Block Diagram of ROM: Descriptions	of ROM MAT
	-	Capacity of User MAT	
	SH74562		
	SH74593	1.5 Mbytes	
2-3	• 12.1 Ov	/erview : Programming/erasing unit	
	Product	Number of 128-Kbytes block	
	SH74562	three blocks	
	SH74593	seven blocks	
	• Figure	12.3 User MAT and Block Allocation	
	Product	Name of 128-Kbytes block	
	SH74562	EB17 to EB19	
	SH74593	EB17 to EB23	
	Added th	ne following blocks	
	Block name	e Read : Start address – Last address	Program/erase : Start address – Last address
	EB20	H'0010 0000 – H'0011 FFFF	H'FD90 0000 – H'FD91 FFFF
	EB21	H'0012 0000 – H'0013 FFFF	H'FD92 0000 – H'FD93 FFFF
	EB22	H'0014 0000 – H'0015 FFFF	H'FD94 0000 – H'FD95 FFFF
	EB23	H'0016 0000 – H'0017 FFFF	H'FD96 0000 – H'FD97 FFFF
	Please refe	er to Appendix D.2.	
2-4	• 12.1 Ov	verview : Protection modes	
	Product	Description	
	SH74562		t memory against programming or erasure: hardware
		protection by the levels on the FWE and	mode pins and software protection by the FENTRY0 bit
		or lock bit settings. The FENTRY0 bit en	ables or disables ROM programming or erasure by the
		FCU.	
	SH74593	This MCU supports two modes to protect	t memory against programming or erasure: hardware
			mode pins and software protection by the FENTRY1 and
			ENTRY1 and FENTRY0 bits enable or disable ROM
		programming or erasure by the FCU.	
2-7	• 12.3.2	Flash Access Status Register (FASTAT) :	Description of ROMAE bit
	Product	Conditions for setting to "1"	
	SH74562		ROM read addresses H'0000 0000 to H'000F FFFF while
		the FENTRYR register value is not H'	
			ddress other than ROM program/erase addresses H'FD80
		0000 to H'FD8F FFFF when the user l	
	SH74593		to ROM program/erase addresses H'FD90 0000 to
			t in the FENTRYR register is "1" in ROM P/E normal
		mode.	
		- An access command is issued to R H'FD97 FFFF while the FENTRY1 bi	OM program/erase addresses H'FD90 0000 to
			ROM read addresses H'0000 0000 to H'0017 FFFF while
		the FENTRYR register value is not H'	
		-	iddress other than ROM program/erase addresses
		H'FD8F 0000 to H'FD80 7FFF when t	the user boot MAT is selected

Please refer to Appendix D.3.

Page	Descriptio	ח
12-12	• 12.3.6	Flash P/E Mode Entry Register (FENTRYR)
	Product	Description
	SH74562	To specify the P/E mode for the ROM so that the FCU can accept commands, set the FENTRY
		bit to "1".
	SH74592	To specify the P/E mode for the ROM so that the FCU can accept commands, set either of bits
		FENTRY1 and FENTRY0 to "1".
	• 12.3.6	Flash P/E Mode Entry Register (FENTRYR) : Description of FEKEY bit
	Product	Description
	SH74562	These bits enable or disable FENTRY0 bit modification. The data written to these bits are not
		retained. These bits are always read as "0".
		H'AA: Enable FENTRY0 bit modification.
		Other than H'AA: Disable FENTRY0 bit modification.
	SH74593	These bits enable or disable bit modification of FENTRY1 and FENTRY0. The data written to
		these bits are not retained. These bits are always read as "0".
		H'AA: Enable bit modification of FENTRY1 and FENTRY0.
		Other than H'AA: Disable bit modification of FENTRY1 and FENTRY0.
12-12	• 12.3.6	Flash P/E Mode Entry Register (FENTRYR) : Description of FENTRY1 bit
	Product	R W Description
	SH74562	0 0 ROM P/E Mode Entry Bit 1
		This bit is not supported by the MCU. Always write "0" to FENTRY1.
	SH74593	R W ROM P/E Mode Entry Bit 1
		These bits specify the P/E mode for the EB20 to EB23 blocks of ROM
		(read addresses: H'0010 0000 to H'0017 FFFF; program/erase
		addresses: H'FD90 0000 to H'FD97 FFFF).
		0: The block of ROM from EB20 to EB23 (0.5Mbytes) is in read mode
		1: The block of ROM from EB20 to EB23 (0.5Mbytes) is in P/E mode
		Programming is enabled when the following conditions are all satisfied:
		- The FWE bit in the FPMON register is "1".
		- The FRDY bit in the FSTATR0 register is "1".
		- H'AA is written to the FEKEY bit in word access.
		[Conditions for clearing to "0"]
		- The FRDY bit in the FSTATR0 register becomes "1" and the FWE bit
		in the FPMON register becomes "0".
		- This register is written to in byte access.
		 A value other than H'AA is written to the FEKEY bit in word access.
		- "0" is written to FENTRY1 while the write enabling conditions are
		satisfied.
		- The FENTRYR register is written to while the FENTRYR register is
		not H'0000 and the write enabling conditions are satisfied.
		[Condition for setting to "1"]
		- "1" is written to the FENTRY1 bit while the write enabling conditions
		are satisfied and the FENTRYR register is H'0000.
	Please ref	er to Appendix D.4.
2-19		12.5 FCU Command Format: Description of Legend
	Product	RA: ROM program/erase address

SH74593 When the FENTRY0 bit is "1": An address in the range from H'FD80 0000 to H'FD8F FFFF When the FENTRY1 bit is "1": An address in the range from H'FD90 0000 to H'FD97 FFFF

SH74562 When the FENTRY0 bit is "1": An address in the range from H'FD80 0000 to H'FD8F FFFF



Page	Descriptio	on
12-20	Figure	12.6 FCU Mode Transition Diagram (ROM-Related Modes)
	Product	Transition from "ROM read mode" to "ROM P/E mode"
	SH74562	FENTRYR = H'0001
	SH74593	FENTRYR = H'0001 or FENTRYR = H'0002
	Please ref	er to Appendix D.5.
12-20		Conditions for FCU Command Acceptance : (1) ROM read mode
	Product	Description
	SH74562	This MCU switches to this mode when the FENTRY0 bit in the FENTRYR register is set to "0".
	SH74593	This MCU switches to this mode when both the FENTRY1 and FENTRY0 bits in the FENTRYR
		register are set to "0".
12-20	• 12.6.2	Conditions for FCU Command Acceptance : (2) ROM P/E mode
	Product	Description
	SH74562	The FCU enters this mode when the FENTRY0 bit is set to "1". Table 12.6 lists the commands that
		the FCU accepts. The high-speed ROM readout operation cannot be used in this mode. Although
		read access to locations H'FD80 0000 to H'FD8F FFFF is illegal, undefined values will be
		returned. To read the ROM data, the FCU must switch to ROM read mode. If a peripheral-bus
		read access to a location from H'FD80 0000 to H'FD8F FFFF is issued in the state where the
		FENTRY0 bit is "1", a ROM access error will occur and the FCU will switch to the command-
		locked state. (See section 12.8.3, Error Protection.)
	SH74593	The FCU enters this mode when either the FENTRY1 or FENTRY0 bit is set to "1". Table 12.6
		lists the commands that the FCU accepts. The high-speed ROM readout operation cannot be used
		in this mode. Although read access to locations H'FD80 0000 to H'FD97 FFFF is illegal, undefined
		values will be returned. To read the ROM data, the FCU must switch to ROM read mode. If a
		peripheral-bus read access to a location from H'FD90 0000 to H'FD97 FFFF is issued in the
		state where the FENTRY1 bit is "1", or If a peripheral-bus read access to a location from
		H'FD80 0000 to H'FD8F FFFF is issued in the state where the FENTRY0 bit is "1", a ROM access
		error will occur and the FCU will switch to the command-locked state. (See section 12.8.3, Error
12-22	. Fierre	Protection.)
12-22	_	12.7 Command State Transitions in ROM Read Mode and P/E mode
	Product	Transition from "ROM read mode" to "ROM P/E mode" FENTRYR = H'0001
		FENTRYR = H'0001 or FENTRYR = H'0002
	011/ 4000	
	Please ref	er to Appendix D.6.
12-23	• 12.6.3	FCU Command Usage: (1) Methods for switching to ROM P/E mode
	Product	Description
	SH74562	For an application to execute ROM related FCU commands, it is necessary to set the FCU to ROM
		P/E mode by setting the FENTRY0 bit in the FENTRYR register. (See section 12.6.2, Conditions for
		FCU Command Acceptance.) To use ROM related FCU commands, set the FENTRY0 bit to "1".
		See section 12.3.6, Flash P/E Mode Entry Register (FENTRYR) for the conditions for setting the
		FENTRY0 bit.
	SH74593	For an application to execute ROM related FCU commands, it is necessary to set the FCU to ROM
		P/E mode by setting bits FENTRY1 and FENTRY0 in the FENTRYR register. (See section 12.6.2,
		Conditions for FCU Command Acceptance.) To use FCU commands for the first 1-Mbyte and
		second 0.5-Mbyte sections of ROM, set bits FENTRY1 and FENTRY0 to the corresponding
		state. See section 12.3.6, Flash P/E Mode Entry Register (FENTRYR) for the conditions for setting
		bits FENTRY1 and FENTRY0.



Page	Descriptio	on
12-23	Figure	12.8 Procedure for Transition to ROM P/E Mode
	Product	Specifies "ROM P/E mode"
	SH74562	To set FENTRY0 to 1 : Write H'AA01
	SH74593	To set FENTRY1 to 1 : Write H'AA02
		To set FENTRY0 to 1 : Write H'AA01
	Please ref	er to Appendix D.7.
12-24	• 12.6.3	FCU Command Usage : (2) Entering ROM Read Mode
	Product	Description
	SH74562	To enable high-speed ROM read access over the SuperHyway bus, it is necessary to set the FCU to ROM read mode by clearing the FENTRYO bit in the FENTRYR register.
	SH74593	To enable high-speed ROM read access over the SuperHyway bus, it is necessary to set the FCU to ROM read mode by clearing bits FENTRY1 and FENTRY0 in the FENTRYR register.
12-25	• 12.6.3	FCU Command Usage : (3) Programming
	Product	Description
	SH74562	The addresses that can be specified in the first to 131st cycles depend on the setting of the FENTRY0 bit in the FENTRYR register. An address in the range from H'FD80 0000 to H'FD8F FFFF is can be specified when the FENTRY0 bit is set to "1". If a command is issued while an illegal combination of the FENTRY0 bit value and addresses is specified, the FCU detects an error and enters command-locked state (see section 12.8.3, Error Protection).
	SH74593	The addresses that can be specified in the first to 131st cycles depend on the setting of bits FENTRY1 and FENTRY0 in the FENTRYR register. An address in the range from H'FD90 0000 to H'FD97 FFFF is can be specified when the FENTRY1 bit is set to "1", or an address in the range from H'FD80 0000 to H'FD8F FFFF is can be specified when the FENTRY0 bit is set to "1". If a command is issued while an illegal combination of FENTRY1 and FENTRY0 bit values and addresses is specified, the FCU detects an error and enters command-locked state (see section 12.8.3, Error Protection).
12-33	• 12.8.1	Hardware Protection : (1) Protection through FWE Pin
	Product	Description
	SH74562	In this state,"1" cannot be written to the FENTRY0 bit in the FENTRYR register; that is, ROM P/E mode cannot be entered, which prevents the ROM from being programmed or erased. When the FRDY bit is set to "1" and the FWE pin is "L" level, the FCU clears the FENTRY0 bit to disable ROM programming and erasure.
	SH74593	In this state,"1" cannot be written to bits FENTRY1 and FENTRY0 in the FENTRYR register; that is, ROM P/E mode cannot be entered, which prevents the ROM from being programmed or erased.
		When the FRDY bit is set to "1" and the FWE pin is "L" level, the FCU clears bits FENTRY1 and FENTRY0 to disable ROM programming and erasure.
12-33	• 12.8.2	Software Protection : (1) FENTRYR Protection
	Product	Description
	SH74562	When the FENTRY0 bit is "0", the EB00 to EB19 blocks of ROM (read addresses: H'0000 0000 to
		H'000F FFFF, program/erase addresses: H'FD80 0000 to H'FD8F FFFF) goes to ROM read mode.
	SH74593	When the FENTRY1 bit in the FENTRYR register is "0", the EB20 to EB23 blocks of ROM
		(read addresses: H'0010 0000 to H'0017 FFFF, program/erase addresses: H'FD90 0000 to H'FD97 FFFF) goes to ROM read mode. When the FENTRY0 bit is "0", the EB00 to EB19 blocks of ROM (read addresses: H'0000 0000 to H'000F FFFF, program/erase addresses: H'FD80 0000
		to H'FD8F FFFF) goes to ROM read mode.

Page	Description							
12-34	Table 12.7 Error Protection Types							
	Product ROM access error							
	SH74562 - A read access command has been issued to addresses H'0000 0000 to H'000F FFFF while the							
	FENTRYR register value is not H'0000.							
	SH74593 - A read access command has been issued to addresses H'FD90 0000 to H'FD97 FFFF while							
	FENTRY1 = "1" in ROM P/E normal mode.							
	- A read access command has been issued to addresses H'0000 0000 to H'0017 FFFF while the							
	FENTRYR register value is not H'0000.							
	Please refer to Appendix D.8.							
13-1	13.1 Overview							
13-2	Figure 13.2 Address Space : Descriptions of 29-bit physical address space (area 6)							
	Product SHwyRAM Capacity (Start address – Last address)							
	SH74562 256 Kbytes(H'1800 0000 – H'1803 FFFF)							
	SH74593 512 Kbytes(H1800 0000 – H1807 FFFF)							
	Please refer to Appendix E.							
13-1	Figure 13.1 Block Diagram of SHwyRAM : Descriptions of Memory block							
	Product Page number [Capacity]							
	SH74562 Page 3 [64 KB]							
	SH74593 Page 7 [64 KB]							
13-2	Figure 13.2 Address Space							
	Product Page							
	SH74562 Page 0 to Page 3							
	SH74593 Page 0 to Page 7							
	Added the following pages							
	Page Address (29-bit physical address)							
	Page 4 H'1804 0000 – H'1804 FFFF							
	Page 5 H'1805 0000 – H'1805 FFFF							
	Page 6 H'1806 0000 – H'1806 FFFF							
	Page 7 H'1807 0000 – H'1807 FFFF							
	Please refer to Appendix E.							
14-1	Table 14.1 Relation between Input Frequency and Input Clock							
	Figure 14.1 Block Diagram of CPG							
	Product PLL frequency multiplier (input to CPU)							
	SH74562 X8.							
	SH74593 X 12 .							
	Please refer to Appendix F.							
14-1	Table 14.1 Relation between Input Frequency and Input Clock							
	Product CPU clock(MHz)							
	SH74562 160.							
	SH74593 240							
45.00	Please refer to Appendix F.							
15-60	Table 15.9 Minimum of Interrupt Response Time: Response time (Minimum)							
	Product NMI IRQ Peripheral Module Remarks							
	SH74562 40lcyc + S × lcyc 36lcyc + S × lcyc 32lcyc + S × lcyc When lcyc:Scyc: Pcyc = 4:2:1							
	SH74593 55 $ cyc + S \times cyc + S $							
	Please refer to Appendix G.							
	i lease lelel to Appendix G.							



Page	Description
28-1	Table 28.1 DRIi Overview
	Product Access areas
	SH74562 All SHwyRAM areas (up to 256 Kbytes)
	SH74593 All SHwyRAM areas (up to 512 Kbytes)
	Please refer to Appendix H.1.
28-46	 28.3.23 DRIi Address Reload Registers 0 and 1 (DRIiADR0RLD and DRIiADR1RLD) : Description of
	DRIADmRLD bit
	Product Description
	SH74562 Address Bits 18 to 2 Reload Value (256-Kbyte area)
	SH74593 Address Bits 18 to 2 Reload Value (512 -Kbyte area)
	Please refer to Appendix H.2.
28-47	28.3.24 DRIi Address Counters 0 and 1 (DRIiADR0CT and DRIiADR1CT) : Description of DRIADn bit
	Product Description
	SH74562 Destination Address Bits 18 to 2 (256-Kbyte area)
	SH74593 Destination Address Bits 18 to 2 (512 -Kbyte area)
	Please refer to Appendix H.3.
29-1	Table 29.1 DRO Module Overview
	Product Access area
	SH74562 SHwyRAM area (256 Kbytes)
	SH74593 SHwyRAM area (512 Kbytes)
	Please refer to Appendix I.
38-1	Table 38.1 Absolute Maximum Ratings
	Product Power dissipation (Pd)
	SH74562 1000 mW ,Ta = -40°C to +125°C
	SH74593 1200 mW ,Ta = -40°C to + 105 °C
	Please refer to Appendix J.1.
PI 28-46 28-46 28-47 28-47 28-47 29-1 29-1 9 38-10 38-1 9 9 38-1 9 19 9 9 8 9 9 9 9 9 9 9 9 9 9 9 9 9 9	Table 38.1 Absolute Maximum Ratings
	Product Operating temperature (Topr)
	SH74562 -40°C to +125°C
	SH74593 –40°C to + 105 °C
	Please refer to Appendix J.1.
38-10	Table 38.14 DC Characteristics - Supply Current
	Product Core supply current (Vdd power supply)
	SH74562 IDD is 480 mA(maximum) Ick = 160 MHz
	SH74593 IDD is 560 mA(maximum) Ick = 240 MHz
	Please refer to Appendix J.2.
38-11	38.3 AC Characteristics: Descriptions of the timing conditions
	Product The timing conditions of AC Characteristics
	SH74562 Ta = -40° C to $+125^{\circ}$ C
	SH74593 Ta = -40°C to + 105 °C
	Please refer to Appendix J.3.



Section 1 Overview

1.2 Product Line Overview

Table 1.2 lists the products.

Table 1.2 Products

Product	Model	ROM Capacity	RAM Capacity	Package	FlexRay
SH74552	R5F74552KBG	1 Mbyte	IL memory: 8 Kbytes,	PRBG0176GA-A	Yes
SH74562	R5F74562KBG		OL memory: 16 Kbytes, and		No
SH74572	R5F74572LBG	_	SHwyRAM: 256 Kbytes		Yes
SH74593	R5F74593LBG	1.5 Mbyte	IL memory: 8 Kbytes,	-	Yes
			OL memory: 16 Kbytes, and SHwyRAM: 512 Kbytes		



Appendix B

Section 1 Overview

1.4 Pin Arrangement

Figure 1.2 shows the pin arrangement.

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	
ł	Vss (N.C.)	PG0/ MOSI0/ TO40	PF5/ SCL/ (CTX3)	PF1/ CTX0	DET3OR5	Vss	PL8/ TIA14/ IRQ7/ DREQ3	PL6/ TIA12/ (TIF1A)	PH15/ DROD7/ TO37/ DDC15	PH13/ DROD5/ (TO35)/ DDC13	PH9/ DROD1/ (TO31)/ DDC09/ CTS2#	PH5/ DROD13/ TO25/ DDC05/ TIA01	PH2/ DROD10/ TO22/ DDC02/ TIF1A	PH0/ DROD8/ TO20/ DDC00/ TIF0A	Vss (N.C.)	A
3	PG1/ MISO0/ TO41	PG2/ RSPCK0/ TO42	PG3/ TO43/ SSL00/ (IRQ7)	PF4/ SDA/ (CRX3)	PF0/ CRX0	ASEBRK#/ BRKACK	PL9/ TIA15/ AUDREVT#	PL5/ TIA11/ (TIF0B)	PL2/ DROWR	PH12/ DROD4/ TO34/ DDC12	PH8/ DROD0/ (TO30)/ DDC08/ RTS2#	PH4/ DROD12/ TO24/ DDC04/ TIA00	PH1/ DROD9/ TO21/ DDC01/ TIF0B	PH3/ DROD11/ TO23/ DDC03/ TIF1B	PK14/ AUDRSYNi	в
С	PG4/ IRQ2/ TO44/ SSL01	Vss	WDTOVF#	Vdd	Vdd	Vdd	PL4/ TIA10/ (TIF0A)	Vss	Vcc	PH14/ DROD6/ (TO36)/ DDC14/ IRQ1	PH10/ DROD2/ (TO32)/ DDC10	PH6/ DROD14/ TO26/ DDC06/ TIA02	PK12/ AUDRD3	PK13/ AUDRCLK	PK11/ AUDRD2	с
D	FWE	RESET#	Vss	Vss	Vdd	Vdd	PL3/ IRQ6	Vss	Vcc	PH11/ DROD3/ (TO33)/ DDC11	PH7/ DROD15/ (TO27)/ DDC07/ TIA03	PK8/ DREQ2	PK9/ AUDRD0/ RTS3#	PK10/ AUDRD1/ CTS3#	PK6/ TXD3	D
E	MD1	NMI	Vss	Vss					•			Vss	PK0/ IRQ5/ SSL10	PK5/ DINC4/ RXD3	PJ14/ TXD1/ MOSI1	Е
F	XTAL	EXTAL	Vss	Vss								Vcc	PJ10/ RXD0/ PWMOFF4/ AD0TRG#	PJ15/ SCK1/ PSPCK1	PJ13/ RXD1/ MISO1	F
G	PLLVss	PLLVcc	MD0	MPMD								PJ1/ (CTX0)/ FTXA	PJ7/ CTX3/ TIF2B/ TXD2	PJ12/ SCK0/ TCLKB/ (IRQ0)	PJ11/ TXD0/ AD0END	G
н	тск	TMS	MD2	TRST#								PJ0/ (CRX0)/ FRXA	PJ4/ CRX2/ FTXENA/ CTS0#	PJ6/ CRX3/ TIF2A/ RXD2/ TIA04	PJ5/ CTX2/ FTXENB/ SCK2	н
J	PD1/ PDIDATA1	TDO	TDI	Vss								PN1/ AD1IN1	PN0/ AD1IN0	PJ3/ CTX1/ FTXB/ RTS0#	PJ2/ CRX1/ FRXB	J
ĸ	PD4/ PDIDATA4	PD3/ PDIDATA3	Vss	Vss								PN4/ AD1IN4	PN5/ AD1IN5	AVss	AVcc	к
L	PD8/ PDIDATA8	PD7/ PDIDATA7	Vcc	Vcc								PM0/ AD0IN0	AVss	AVREFL	AVREFH	L
м	PD9/ PDIDATA9	PD6/ PDIDATA6	PD0/ PDIDATA0	Vss	Vss	Vss	Vdd	Vdd	PC6/ CLKOUT/ TO36	Vcc	Vss	AVss	PM4/ AD0IN4	AVREFL	AVREFH	М
N	PD10/ PDIWR	PD5/ PDIDATA5	PA4/ TO04/ DDB04	PA7/ TO07/ DDB07	PA10/ TO12/ DDB10/ PSLDATA0	PA11/ TO13/ DDB11/ PSLDATA1	Vdd	Vdd	PC1/ TO31/ MISO2	Vcc	Vss	PM2/ AD0IN2	PM6/ AD0IN6	PM9/ AD0IN9	AVss	N
P	PD2/ PDIDATA2	PA3/ TO03/ DDB03	PA0/ TO00/ DDB00	PA2/ TO02/ DDB02	PA6/ TO06/ DDB06	PA9/ TO11/ DDB09/ PSLCLKA	PA13/ TO15/ DDB13/ PSLDATA3	PB1/ PWMOFF1 DINB1	PC0/ TO30/ MOSI2/ (IRQ6)	PC3/ TO33/ SSL20/ IRQ0	PM15/ AD0IN15	PM13/ AD0IN13	PM11/ AD0IN11	PM8/ AD0IN8	AVcc	Ρ
۲	Vss (N.C.)	PE15/ TO27/ PSLCLR	PA1/ TO01/ DDB01	PA5/ TO05/ DDB05	PA8/ TO10/ DDB08/ PSLCLKB	PA12/ TO14/ DDB12/ PSLDATA2	PB0/ PWMOFF0/ DINB0	PB3/ PWMOFF3 DINB3	PC2/ TO32/ RSPCK2/ DREQ0	PC5/ TO35	PC14	PM14/ AD0IN14	PM12/ AD0IN12	PM10/ AD0IN10	AVcc (N.C.	R
-	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	-

Figure 1.2 Pin Arrangement (Top Transparent View)

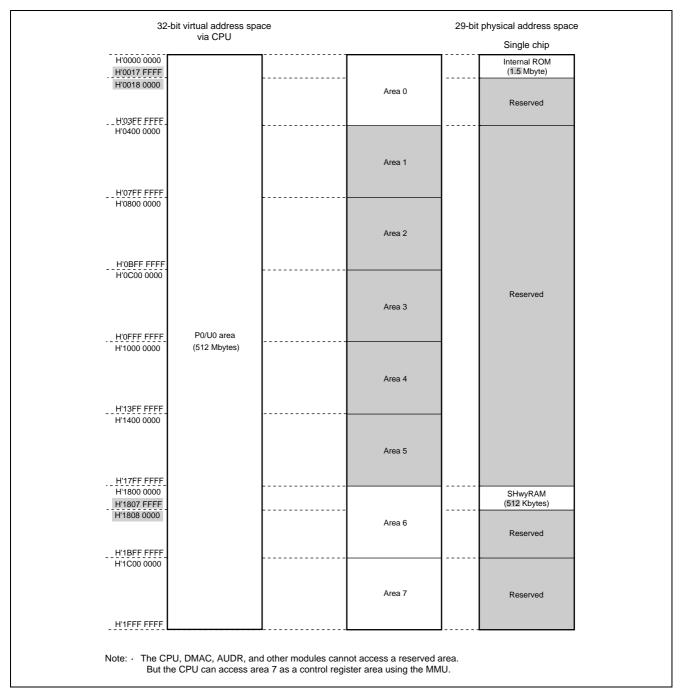


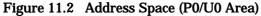
Appendix C

Appendix C.1

Section 11 Address Space

For details on the P0/U0 area to the P4 area, see figures 11.2 to 11.6.







Section 11 Address Space

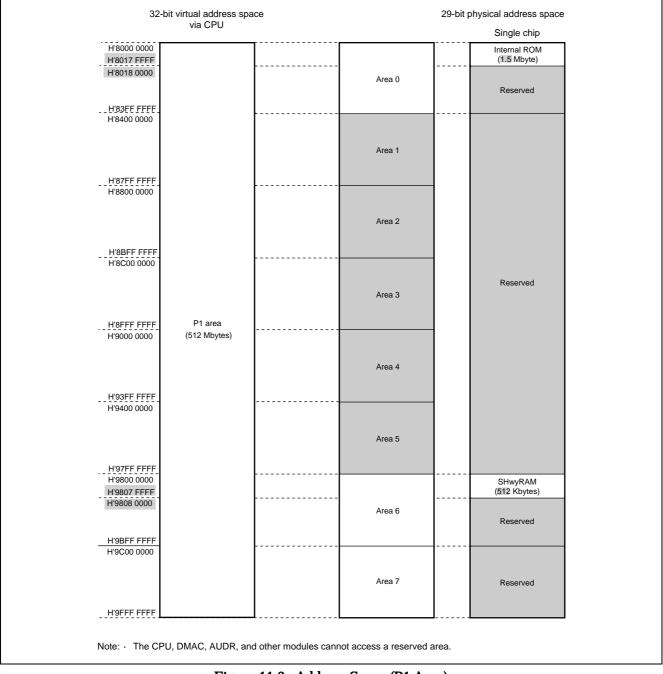


Figure 11.3 Address Space (P1 Area)



Section 11 Address Space

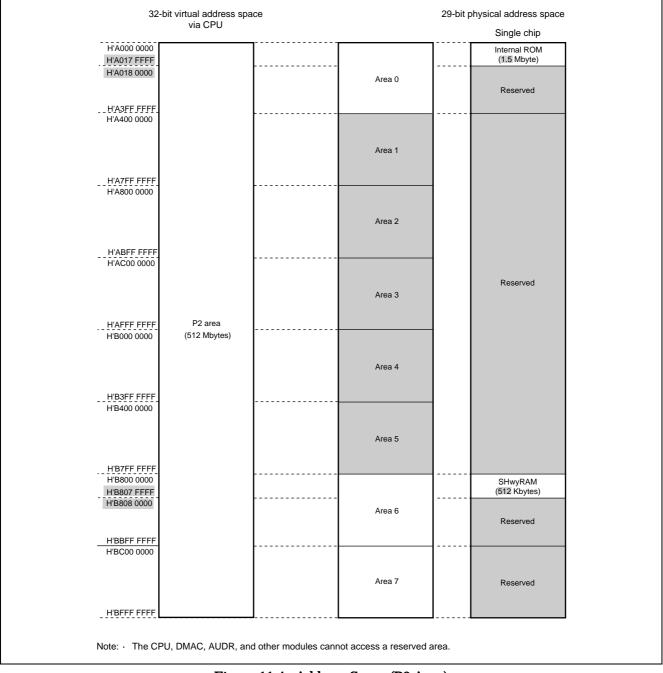


Figure 11.4 Address Space (P2 Area)



Section 11 Address Space

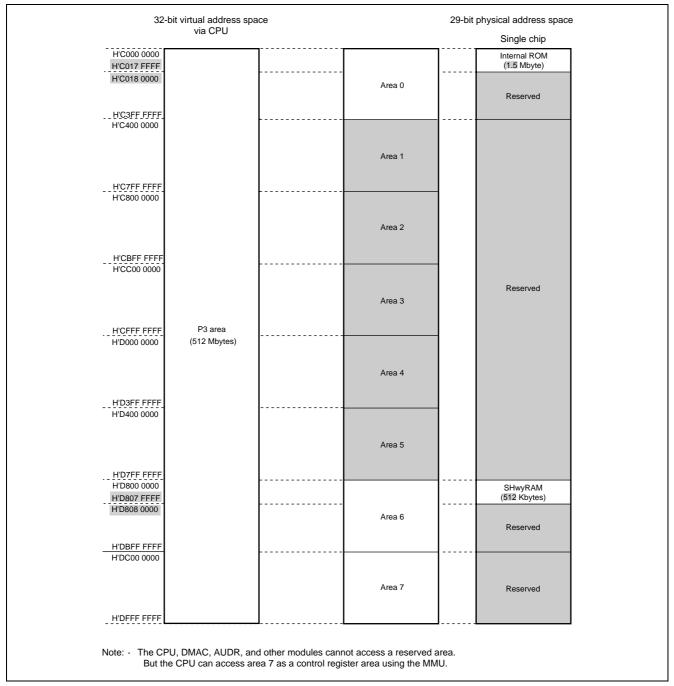


Figure 11.5 Address Space (P3 Area)

Section 12 ROM

Appendix D.1

12.1 Overview

• Two types of flash-memory MATs

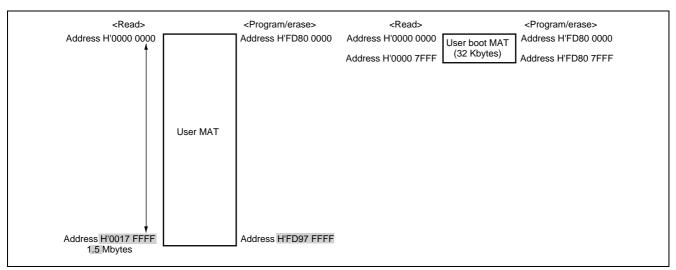


Figure 12.1 Memory MAT Configuration in ROM



12.1 Overview

• Programming/erasing unit Figure 12.3 shows the block allocation of the user MAT.

H'0000 0000 H'0000 1FFF	EB00 (8-Kbyte)	H'FD80 0000 H'FD80 1FFF				
H'0000 2000	EB01 (8-Kbyte)	H'FD80 2000	<read></read>		<program erase=""></program>	
H'0000 3FFF H'0000 4000		H'FD80 3FFF H'FD80 4000	Block start	Block name (size)	Block start	
H'0000 5FFF H'0000 6000	EB02 (8-Kbyte)	H'FD80 5FFF H'FD80 6000	Block end	Biook name (6120)	Block end	
H'0000 7FFF H'0000 8000	EB03 (8-Kbyte)	H'FD80 7FFF H'FD80 8000	<u> </u>			
H'0000 9FFF	EB04 (8-Kbyte)	H'FD80 9FFF				
H'0000 A000 H'0000 BFFF	EB05 (8-Kbyte)	H'FD80 A000 H'FD80 BFFF	_			
H'0000 C000 H'0000 DFFF	EB06 (8-Kbyte)	H'FD80 C000 H'FD80 DFFF	H'0010 0000		H'FD90 0000	
H'0000 E000 H'0000 FFFF	EB07 (8-Kbyte)	H'FD80 E000 H'FD80 FFFF				
H'0001 0000		H'FD81 0000		EB20 (128-Kbyte)		
	EB08 (64-Kbyte)	H'FD81 FFFF				
H'0001 FFFF H'0002 0000		H'FD82 0000	H'0011 FFFF H'0012 0000		H'FD91 FFFF H'FD92 0000	
	EB09 (64-Kbyte)					
H'0002 FFFF H'0003 0000		H'FD82 FFFF H'FD83 0000		EB21 (128-Kbyte)		
110000 0000	EB10 (64-Kbyte)	111 200 0000		2021 (120 103)(0)		
H'0003 FFFF	EBT0 (011kbykb)	H'FD83 FFFF	H'0013 FFFF		H'FD93 FFFF	
H'0004 0000		H'FD84 0000	H'0014 0000		H'FD94 0000	
H'0004 FFFF	EB11 (64-Kbyte)	H'FD84 FFFF				
H'0005 0000		H'FD85 0000		EB22 (128-Kbyte)		
	EB12 (64-Kbyte)					
H'0005 FFFF H'0006 0000		H'FD85 FFFF H'FD86 0000	H'0015 FFFF		H'FD95 FFFF	
	EB13 (64-Kbyte)		H'0016 0000		H'FD96 0000	
H'0006 FFFF	EBTO (OTTOSTO)	H'FD86 FFFF		EP22 (128 Khuta)		
H'0007 0000		H'FD87 0000		EB23 (128-Kbyte)		
H'0007 FFFF	EB14 (64-Kbyte)	H'FD87 FFFF	H'0017 FFFF		H'FD97 FFFF	
H'0008 0000		H'FD88 0000	1100171111		11100/1111	
H'0008 FFFF	EB15 (64-Kbyte)	H'FD88 FFFF				
H'0009 0000		H'FD89 0000				
	EB16 (64-Kbyte)					
H'0009 FFFF H'000A 0000		H'FD89 FFFF H'FD8A 0000				
11000A 0000		111 DOA 0000				
	EB17 (128-Kbyte)					
	(c					
H'000B FFFF		H'FD8B FFFF				
H'000C 0000		H'FD8C 0000				
	EB18 (128-Kbyte)					
H'000D FFFF H'000E 0000		H'FD8D FFFF H'FD8E 0000				
	EB19 (128-Kbyte)					
H'000F FFFF		H'FD8F FFFF				

Figure 12.3	User MAT and Block Allocation
-------------	-------------------------------



12.3.2 Flash Access Status Register (FASTAT)

The FASTAT register indicates the access error status for the ROM. If any bit in the FASTAT register is set to "1", the FCU enters command-locked state (see section 12.8.3, Error Protection). To cancel a command-locked state, set the FASTAT register to H'10, and then issue a status-clear command to the FCU.

	Flas	h Acces	s Status	s Reg	ister	(FAS	STAT)					<p4 a810="" address:="" h'fdff="" location=""></p4>
		Bit:	7	6		5	4	3	2	1	0	_
			ROM AE	—	-		CMD LK	_	_	_		
	After	Reset:	0	0		0	0	0	0	0	0	
												<after h'00="" reset:=""></after>
	D:4	1 h h		lan		After		14/				Description
7	Bit	RON	oreviat ₄៱⊏	lion	0 0	ese	tR R	W *1	Acce	ss Err	or Bit	Description
,							κ		Indica bit be and t 0: No 1: A f [Cond • W [Cond • A a ir • A H F	ates w ecome he FC ROM ROM a dition f /hen " ditions read ddres read the F read read FD80 ENTR	thether s "1", 1 U enter access for clea 0" is w for se access ses H ENTR access 0000 YR res	r or not a ROM access error has been generated. If this the ILGLERR bit in the FSTATR0 register is set to "1" ers a command-locked state. ss error has occurred. aring to "0"] written after reading out ROMAE with the value "1". etting to "1"] ss command is issued to ROM program/erase 'FD90 0000 to H'FD97 FFFF while the FENTRY1 bit RYR register is "1" in ROM P/E normal mode. s command is issued to ROM program/erase addresses to H'FD8F FFFF while the FENTRY0 bit in the gister is "1" in ROM P/E normal mode.
									a	ddres	ses H	'FD90 0000 to H'FD97 FFFF while the FENTRY1 bit RYR register is "0".
									Н	'FD80	0000	mmand is issued to ROM program/erase addresses to H'FD8F FFFF while the FENTRY0 bit in the gister is "0".
									0		H'001	s command is issued to ROM read addresses H'0000 I 7 FFFF while the FENTRYR register value is not
												e, program, or lock bit program command is issued to ne user boot MAT is selected.
									р	rogran	n/eras	mmand is issued to an address other than ROM e addresses H'FD80 0000 to H'FD80 7FFF when the T is selected.
6, 5	5	_			All	0	0	0		rved E e bits		ways read as "0". The write value should always be "0".



		After			
В	it Abbreviation	Reset	R	W	Description
4	CMDLK	0	R		FCU Command Lock Bit
					Indicates whether the FCU is in command-locked state (see section
					12.8.3, Error Protection).
					0: The FCU is not in a command-locked state
					1: The FCU is in a command-locked state
					[Condition for clearing to "0"]
					• The FCU completes the status-clear command processing while the
					FASTAT register is H'10.
					[Condition for setting to "1"]
					The FCU detects an error and enters command-locked state.
3 to 0		All 0	0	0	Reserved Bits
					These bits are always read as "0". The write value should always be "0".

Note: *1 Writing a "0" after reading a "1" is only allowed in order to clear the flag.



12.3.6 Flash P/E Mode Entry Register (FENTRYR)

The FENTRYR register specifies the P/E mode for the ROM. Writing to the FENTRYR register is enabled only when a specified value is written to the high-order byte. Writing any other value initializes this register. To specify the P/E mode for the ROM so that the FCU can accept commands, set **either of bits FENTRY1 and FENTRY0** to "1". Note that if this register is set to a value other than H'0001 or H'0002, the ILGLERR bit in the FSTATR0 register will be set to "1" and the FCU will switch to the command-locked state.

The FENTRYR register can be initialized by a hardware reset, or setting the FRESET bit in the FRESETR register to "1".

Flash P/E Mode Entry Register (FENTRYR) <P4 address: location H'FDFF A902> Bit: FENT RY0 FENT FEKEY RY1 After Reset:

<After Reset: H'0000>

		After			
Bit	Abbreviation	Reset	R	W	Description
15 to 8	FEKEY	All 0	0	W	FENTRYR Register Write Key Code Bits
					These bits enable or disable bit modification of FENTRY1 and
					FENTRY0. The data written to these bits are not retained. These bits are
					always read as "0". H'AA: Enable bit modification of FENTRY1 and FENTRY0.
					Other than H'AA: Disable bit modification of FENTRY1 and FENTRY0.
7 to 2		All 0	0	0	Reserved Bits
1 10 2		7 11 0	Ū	U	These bits are always read as "0". The write value should always be "0".
1	FENTRY1	0	R	w	ROM P/E Mode Entry Bit 1
•		•			These bits specify the P/E mode for the EB20 to EB23 blocks of
					ROM (read addresses: H'0010 0000 to H'0017 FFFF; program/erase
					addresses: H'FD90 0000 to H'FD97 FFFF).
					0: The block of ROM from EB20 to EB23 (0.5Mbytes) is in read mode
					1: The block of ROM from EB20 to EB23 (0.5Mbytes) is in P/E mode
					Programming is enabled when the following conditions are all
					satisfied:
					 The FWE bit in the FPMON register is "1".
					 The FRDY bit in the FSTATR0 register is "1".
					 H'AA is written to the FEKEY bit in word access.
					[Conditions for clearing to "0"]
					• The FRDY bit in the FSTATR0 register becomes "1" and the FWE
					bit in the FPMON register becomes "0".
					 This register is written to in byte access.
					A value other than H'AA is written to the FEKEY bit in word
					access.
					 "0" is written to FENTRY1 while the write enabling conditions
					are satisfied.
					• The FENTRYR register is written to while the FENTRYR register
					is not H'0000 and the write enabling conditions are satisfied.
					[Condition for setting to "1"]
					 "1" is written to the FENTRY1 bit while the write enabling
					conditions are satisfied and the FENTRYR register is H'0000.



			After			
	Bit	Abbreviation	Reset	R	W	Description
0		FENTRY0	0	R	W	ROM P/E Mode Entry Bit 0
						These bits specify the P/E mode for the EB00 to EB19 blocks of ROM
						(read addresses: H'0000 0000 to H'000F FFFF; program/erase
						addresses: H'FD80 0000 to H'FD8F FFFF).
						0: The block of ROM from EB00 to EB19 (1Mbyte) is in read mode
						1: The block of ROM from EB00 to EB19 (1Mbyte) is in P/E mode
						Programming is enabled when the following conditions are all satisfied:
						 The FWE bit in the FPMON register is "1".
						 The FRDY bit in the FSTATR0 register is "1".
						H'AA is written to the FEKEY bit in word access.
						[Conditions for clearing to "0"]
						• The FRDY bit in the FSTATR0 register becomes "1" and the FWE bit in the FPMON register becomes "0".
						This register is written to in byte access.
						• A value other than H'AA is written to the FEKEY bit in word access.
						• "0" is written to the FENTRY0 bit while the write enabling conditions are satisfied.
						• The FENTRYR register is written to while the FENTRYR register is not H'0000 and the write enabling conditions are satisfied.
						[Condition for setting to "1"]
						• "1" is written to FENTRY0 while the write enabling conditions are
						satisfied and the FENTRYR register is H'0000.



12.6.2 Conditions for FCU Command Acceptance

Figure 12.6 is an FCU mode transition diagram.

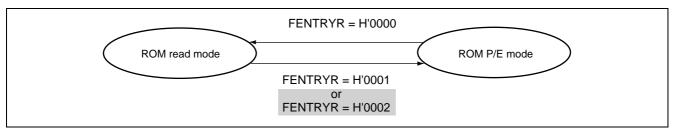
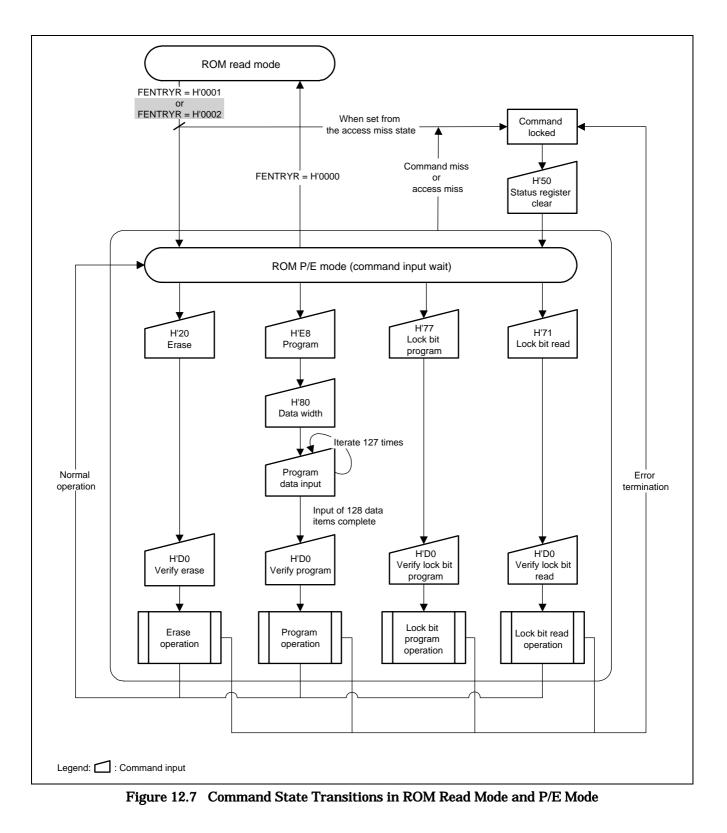


Figure 12.6 FCU Mode Transition Diagram (ROM-Related Modes)



12.6.2 Conditions for FCU Command Acceptance

(2) ROM P/E mode



12.6.3 FCU Command Usage

(1) Methods for switching to ROM P/E mode

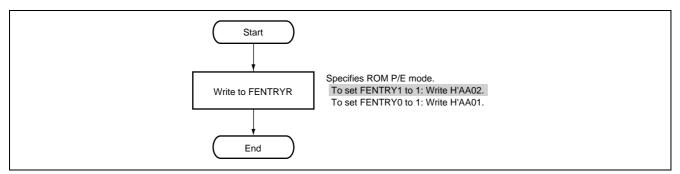


Figure 12.8 Procedure for Transition to ROM P/E Mode



12.8.3 Error Protection

Table 12.7 Error Protection Types

Error	Description	ILGLERR bit	ERSERR bit	PRGERR bit	FCUERR bit	FRDTCT bit	ROMAE bit
FENTRYR setting error	The key code (H'AA) has been supplied as the upper 8 bits of the FENTRYR register but the value of the lower 8 bits is other than H'01 or H'02.	1	0	0	0	0	0
Illegal command error	An undefined code has been specified in the first cycle of an FCU command.	1	0	0	0	0	0
	The value specified in the last of the multiple cycles of an FCU command is not H'D0.	1	0	0	0	0	0
	The value specified in the second cycle of a program command is not H'80.	1	0	0	0	0	0
	A command has been issued in command-locked state.	1	0/1	0/1	0/1	0/1	0/1
Erasure error	An error has occurred during erasure processing.	0	1	0	0	0	0
	A block erase command has been issued for the erasure block whose lock bit is set to "0" while the FPROTCN bit in the FPROTR register is "0".	0	1	0	0	0	0
Programming error	An error has occurred during programming processing.	0	0	1	0	0	0
	A program or lock bit program command has been issued for the erasure block whose lock bit is set to "0" while the FPROTCN bit in the FPROTR register is "0".	0	0	1	0	0	0
FCU error	An error has occurred during CPU processing in the FCU.	0	0	0	1	0	0
ROM access error	A read access command has been issued to addresses H'FD90 0000 to H'FD97 FFFF while FENTRY1 = "1" in ROM P/E normal mode.	1	0	0	0	0	1
	A read access command has been issued to addresses H'FD80 0000 to H'FD8F FFFF while FENTRY0 = "1" in ROM P/E normal mode.	1	0	0	0	0	1
	An access command has been issued to addresses H'FD90 0000 to H'FD9F FFFF while FENTRY1 = "0".	1	0	0	0	0	1
	An access command has been issued to addresses H'FD80 0000 to H'FD8F FFFF while FENTRY0 = "0".	1	0	0	0	0	1
	A read access command has been issued to addresses H'0000 0000 to H'0017 FFFF while the FENTRYR register value is not H'0000.	1	0	0	0	0	1
	A ROM programming or erasing command (program, lock bit program, or block erase command) has been issued while the user boot MAT is selected.	1	0	0	0	0	1
	An access command has been issued to an address other than the addresses for ROM programming/erasure H'FD80 0000 to H'FD80 7FFF while the user boot MAT is selected.	1	0	0	0	0	1



Appendix E

Section 13 SuperHyway RAM (SHwyRAM)

13.1 Overview

As shown in figure 13.2, the SHwyRAM is allocated to the upper **512** Kbytes of area 6 (H'1800 0000 to **H'1807 FFFF** in the 29-bit physical address space).

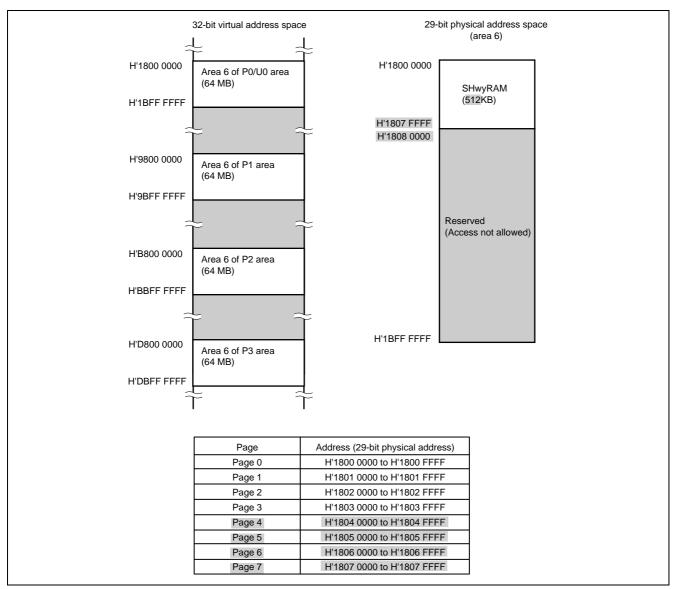


Figure 13.2 Address Space



Appendix F

Section 14 Clock Generator (CPG)

14.1 Overview

Table 14.1 lists the relation between input frequency and input clock.

Table 14.1 Relation between Input Frequency and Input Clock

	PLL frequency					
Input frequency (MHz)	multiplier (input to CPU)	CPU clock (MHz)	SHwy clock (MHz)	Peripheral clock (MHz)	Peripheral A clock (MHz)	FlexRay clock (MHz)
20	×12	240	80	40	80	80



Appendix G

Section15 Interrupt Controller (INTC)

15.5 Interrupt Response Time

Table 15.9 shows the interrupt response time, which is the interval from when an interrupt request occurs until the interrupt exception handling is started and the start instruction of the interrupt handling is fetched.

Table 15.9 Interrupt Response Time

		Number of State					
Item		NMI	IRQ	Peripheral Module	Remarks		
Priority determinat	tion time	7 Pcyc	6 Pcyc	5Pcyc			
Wait time until the current sequence	CPU finishes the		S-1 (≥ 0) × Icyc				
handling begins (s a SHwy bus reque	n interrupt exception aving SR and PC) until est is issued to fetch the the interrupt handling		11lcyc + 1Scyc				
Response time	Total	(S + 10) lcyc + 1Scyc + 7 Pcyc	(S + 10) lcyc + 1Scyc + 6 Pcyc	(S + 10) lcyc + 1Scyc + 5Pcyc			
	Minimum	55lcyc + S × lcyc	49lcyc + S × lcyc	43lcyc + S × lcyc	When Icyc:Scyc: Pcyc = 6 :2:1		

Legend:

Icyc: Period for one CPU clock cycle

Scyc: Period for one SHwy clock cycle

Pcyc: Period for one peripheral clock cycle

S: Number of instruction execution states



Appendix H

Section 28 Direct RAM Input Interface (DRI)

Appendix H.1

28.1 Overview

Table 28.1 lists the overview of the DRIi modules.

Table 28.1 DRIi Overview

Item	Description
Number of channels	3 channels
Operating frequency	80 MHz (when PAck = 80 MHz)
Transfer method	Clock synchronous parallel input
Access areas	All SHwyRAM areas (up to 512 Kbytes)
Maximum transfer rate	80 Mbytes/second (when the DRIi operating frequency is 80 MHz)
Minimum data acquisition	The following are the minimum periods when the DRIi operating frequency is 80 MHz.
period	43.75 ns (special mode disabled and the input data bus width is 8 or 16 bits)
	25 ns (special mode enabled)
Data acquisition bus width	8 or 16 bits
Event counter	16 bits \times 6 counters (DEC5 to DEC0)
Bank switching function	Two banks can be specified as the data storage destination in SHwyRAM
Data acquisition edges	Either rising edges, falling edges, or both edges can be selected
Acquisition timing adjustment	Sets the time between detection of the data acquisition edge and the acquisition
function	operation
Decimation control function	Data can be acquired selectively using an event counter (DEC5 to DEC0)



28.3.23 DRIi Address Reload Registers 0 and 1 (DRIiADR0RLD and DRIiADR1RLD)

DRIiADR0CT and DRIiADR1CT are registers that hold counter reload values. When reload mode is selected with the DRIi transfer control register (DRIiTRMCNT) ADMD (address counter operating mode selection) bit, the corresponding DRIi address counters are reloaded with the values set in these registers when the DRIi data acquisition control register (DRIiDCAPCNT) DCPEN (acquisition enable) bit changes from "0" to "1".

Note: • These registers may only be rewritten when the DRIi data acquisition control register (DRIiDCAPCNT) DCPEN (acquisition enable) bit is in the "0" state.

DRI1 Addres DRI2 Addres	s Relo	ad Reg	ister 0	(DRI1A		.D)						<p4 a<="" th=""><th>ddress</th><th>locatio</th><th>on H'FF</th><th>BF C024> BF D024> BF E024></th></p4>	ddress	locatio	on H'FF	BF C024> BF D024> BF E024>
Bit:	31	30	29	28	27	26	25	24	23	22	21	20	19	18	17	16
	_	_	_	_	_	_	_	_	_			_	_	DI	RIADOF	RLD
After Reset:	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
Bit:	15	14	13	12	11	10	9	8	7	6	5	4	3	2	1	0
							DRIAD	DORLD								_
After Reset:	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0	0
DRI2 Addres			ister 1 ister 1													BF D02C> BF E02C>
							25	24	23	22	21			locatio		BF E02C>
DRI2 Addres	s Relo	ad Reg	ister 1	DRI2A	DR1RL	.D)	25 — 0	24 — 0	23 — 0	22 — 0	21 — 0	<p4 a<="" td=""><td>ddress:</td><td>locatio</td><td>n H'FF 17</td><td>BF E02C></td></p4>	ddress:	locatio	n H'FF 17	BF E02C>
DRI2 Addres	31	ad Reg 30	29	(DRI2A 28	27	.D) 26 —	_	_	_	_	—	<p4 ac<="" td=""><td>ddress: 19 —</td><td>locatio 18 Di</td><td>n H'FF 17 RIAD1F</td><td>BF E02C></td></p4>	ddress: 19 —	locatio 18 Di	n H'FF 17 RIAD1F	BF E02C>
DRI2 Addres Bit: After Reset:	s Relo 31 — 0	ad Reg 30 — 0	29 0	(DRI2A 28 — 0	DR1RL 27 0	D) 26 — 0	0 9	0	0	0	0	<p4 ac<br="">20 — 0</p4>	19 0	locatio 18 Df 0	n H'FF <u>17</u> RIAD1F 0	BF E02Č> <u>16</u> RLD 0
DRI2 Addres Bit: After Reset:	s Relo 31 — 0	ad Reg 30 — 0	29 0	(DRI2A 28 — 0	DR1RL 27 0	D) 26 — 0	0 9	0 8	0	0	0	<p4 ac<br="">20 — 0</p4>	19 0	locatio 18 Df 0	n H'FF <u>17</u> RIAD1F 0	BF E02Č> <u>16</u> RLD 0
DRI2 Addres Bit: After Reset: Bit: After Reset:	s Relo 31 0 15 0	ad Reg 30 0 14 0	ister 1 29 0 13 0	(DRI2A 28 0 12 0	DR1RL 27 — 0 11	D) <u>26</u> 0 10 0	0 9 DRIAE	0 8 01RLD	0 7	0 6	0 5 0	<p4 ad<br="">20 — 0 4</p4>	ddress: 19 0 3 0 <	locatio 18 DI 0 2 0	n H'FF <u>17</u> RIAD1F 0 1 0	BF E02C> <u>16</u> <u>3LD</u> 0 0 0
DRI2 Addres Bit: After Reset: Bit: After Reset:	s Relo 31 0 15 0	ad Reg 30 0 14 0 0	ister 1 29 0 13 0	(DRI2A 28 0 12 0	DR1RL 27 0 11 0	D) <u>26</u> 0 <u>10</u> 0	0 9 DRIAE	0 8 D1RLD 0	0 7	0 6	0 5 0	<p4 ad<br="">20 0 4 0</p4>	ddress: 19 0 3 0 <	locatio 18 DI 0 2 0	n H'FF <u>17</u> RIAD1F 0 1 0	BF E02C> 16 RLD 0 0 0 0 0
DRI2 Addres Bit: After Reset: Bit: After Reset: it Abbr	s Relo 31 0 15 0	ad Reg 30 0 14 0 0	ister 1 29 0 13 0	(DRI2A 28 0 12 0	DR1RL 27 0 11 0 R M	D) 26 0 10 0 0 Res	0 9 DRIAE 0	0 8 D1RLD 0 Bits	0 7 0	0 6 0	0 5 0 Des	<p4 ad<br="">20 0 4 0 criptic</p4>	19 0 3 0	locatic 18 Df 0 2 0 After I	n H'FF 17 RIAD1F 0 1 0 Reset:	BF E02C> 16 RLD 0 0 0 0 0

Reserved Bits

These bits are always read as "0". The write value should always be "0".

Legend: m = 0 or 1

All 0

0 0

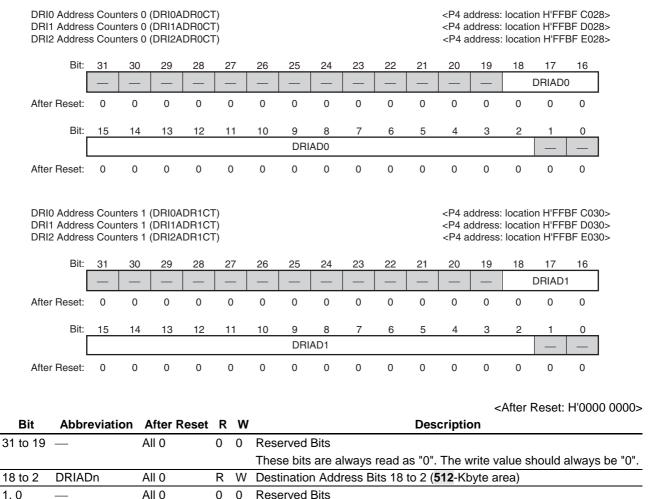
1,0



28.3.24 DRIi Address Counters 0 and 1 (DRIiADR0CT and DRIiADR1CT)

The DRIiADR0CT and DRIiADR1CT counters are provided to specify bits A18 to A2 of the address in SHwyRAM that is the DRIi module transfer destination. Bits A31 to A19 are fixed at "0". These counters are incremented by "4" each time a DRIi transfer completes. There are two DRIi address counter operating modes, and applications can select the mode with the DRIi transfer control register (DRIiTRMCNT) ADMD bit. See the documentation of the DRIi transfer control register (DRIiTRMCNT) for details.

- Notes: If a DRIi address counter value is a value other than an area in which SHwyRAM is located, the DRIi module will behave as though the DRIi transfers complete, but no writes of the acquired data will be performed whatsoever.
 - A DRIi address counter is incremented by "4" when a DRIi transfer completed. This is performed for the one that is active at that time according to the setting of the DRIi transfer control register (DRIiTRMCNT) ADSL (address counter selection) bit.
 - These registers must only be rewritten in the state where a DRIi transfer counter (DRIiTRMCT) underflow has occurred (the counter is stopped at the value H'0000 0000).



These bits are always read as "0". The write value should always be "0".

Legend: n = 0 or 1



Appendix I

Section 29 Direct RAM Output Interface (DRO)

29.1 Overview

Table 29.1 lists the overview of the DRO module.

Table 29.1 DRO Module Overview

Item	Description
Transfer method	Parallel strobed output
Access area	SHwyRAM area (512 Kbytes)
Output data width	Either 8-bits or 16-bits
Maximum transfer clock	10 MHz
Maximum transfer rate	20 Mbytes/s (when 16 bits is selected, Pck = 40MHz)
Strobe polarity	Either "H" active or "L" active may be selected.
Timing adjustment function	The setup and hold times can be programmed in 1Pck units relative to the strobe signal edge.
Interrupt request	An interrupt request is generated after a prespecified number of data items have been output.



Appendix J

Section 38 Electrical Characteristics

Appendix J.1

38.1 Absolute Maximum Ratings

Table 38.1 shows the absolute maximum ratings.

Table 38.1 Absolute Maximum Ratings

ltem		Symbol	Rating	Unit	Remarks	
Power supply V _{dd}		Vdd	-0.3 to +2.0	V		
voltage V	cc, PLLVcc	Vcc	–0.3 to +6.5	V		
Input voltage V	cc power supply related	Vin	-0.3 to Vcc +0.3	V		
р	ins					
Analog supply v	oltage	AVcc	–0.3 to +6.5	V		
Analog reference voltage		AVREFH	-0.3 to AVcc +0.3	V	AVREFH > AVREFL	
		AVREFL	-0.3 to AVss +0.3	V		
Analog input vol	tage	VAN	-0.3 to AVcc +0.3	V		
Vss differential	voltage	Vss – PLLVss	-0.1 to +0.1	V		
		Vss – AVss	-0.1 to +0.1	V		
		PLLVss – AVss	-0.1 to +0.1	V		
Maximum input	Digital input pins	Imax	-20 to +20	mA		
current per pin*2	Analog input pins	Imax	-20 to +20	mA		
(per pin)						
Power dissipation	n	Pd	1200	mW	Ta = -40°C to + 105 °C	
Operating temperature*1		topr	–40 to + 105	°C		
Storage temperature		tstg	–55 to +125	°C	Before assembly	

[Usage Notes]

Operating the MCU in excess of the absolute maximum ratings may result in permanent damage. Be sure to use the MCU in compliance with the connection of power pins, combination conditions of applicable power supply voltages, voltage applicable to each pin, and conditions of output voltage, as specified in the manual. Connecting a non-specified power supply or using the MCU at an incorrect voltage may result in permanent damage of the MCU or the system that contains the MCU.

- Notes: *1 This does not guarantee that the microcomputer can operate continuously at 85°C-plus. Consult Renesas if the microcomputer is going to be used for 85°C-plus applications.
 - *2 Ensure that the current input duration does not exceed 10 ms and that the total current input does not exceed 100 mA.



Section 38 Electrical Characteristics

Table 38.14 DC Characteristics - Supply Current

Recommended Operating Conditions: Vcc = PLLVcc = $5.0 \text{ V} \pm 0.5 \text{ V}/3.3 \text{ V} \pm 0.3 \text{ V}$, AVcc = $5.0 \text{ V} \pm 0.5 \text{ V}/3.3 \text{ V} \pm 0.3 \text{ V}$

Item	Symbol	Min.	Тур.	Max.	Unit	Measurement Conditions	
Core supply current (V	I _{DD}	_	_	560	mA	lck = 240 MHz	
System consumption of supply)* ¹ (Including fla programming and eras	I _{CC}	_	_	90	mA	Pck = 40 MHz	
PLL supply current (PLLVcc power supply)		I _{PLL}	_	_	10	mA	
Analog supply current (AVcc power supply)	During A/D conversion	I _{AVcc}	_	_	10	mA	2 modules,
	Awaiting A/D conversion		_	_	1	mA	Pck = 40MHz
ADC reference power supply current (AVREF)	During A/D conversion	I _{AVREF}			4	mA	2 modules,
	Awaiting A/D conversion		_	_	3.5	mA	Pck = 40MHz

Notes: *1 An inrush current of about 100 mA will be caused at power on.

• When the A/D converter is not used, do not leave the AVcc, AVref, and AVss pins open.

• The supply current is measured when V_{IH} min = Vcc - 0.5 V, V_{IL} = 0.5 V, with all output pins unloaded.



Section 38 Electrical Characteristics

38.3 AC Characteristics

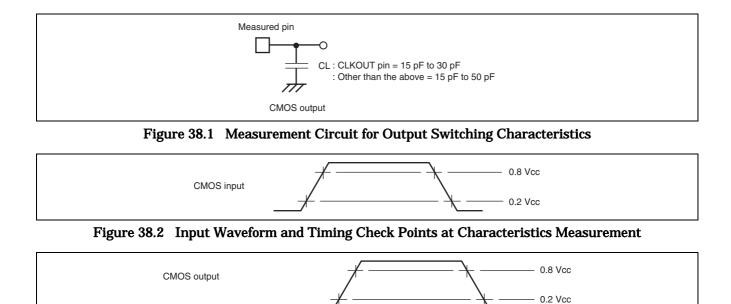
• The timing conditions without specifications are the following :

 $Vdd = 1.5 V + 0.15 V, -0.1 V, Vcc = PLLVcc = 5.0 V \pm 0.5 V/3.3 V \pm 0.3 V, AVcc = 5.0 V \pm 0.5 V/3.3 V \pm 0.3 V, AVREFH = 4.5 V to AVcc/3.0 V to AVcc,$

 $Vss = PLLVss = AVss = AVREFL = 0 V, Ta = -40^{\circ}C to +105^{\circ}C$

When not otherwise specified, the input threshold value is the value under conditions where all module input pins for the same channel are set to the same characteristics. When not otherwise specified, the output driving ability is the value under conditions where all module output pins for the same channel are set to the same characteristics.

• Standard values are guaranteed when the output load capacity of the measurement pin is 15 pF to 50 pF. Note that the output load capacity of the CLKOUT pin is 15pF to 30pF.



Note: • For details on CLKOUT output timing check points at characteristics measurement, refer to each figure in this section.

Figure 38.3 Output Timing Check Points at Characteristics Measurement



REVISION HISTORY

SH74593 Datasheet

		Description			
Rev.	Date	Page	Summary		
1.20	Sep 10, 2012	-	First edition issued		

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General Precautions in the Handling of MPU/MCU Products

The following usage notes are applicable to all MPU/MCU products from Renesas. For detailed usage notes on the products covered by this manual, refer to the relevant sections of the manual. If the descriptions under General Precautions in the Handling of MPU/MCU Products and in the body of the manual differ from each other, the description in the body of the manual takes precedence.

1. Handling of Unused Pins

Handle unused pins in accord with the directions given under Handling of Unused Pins in the manual.

- The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible. Unused pins should be handled as described under Handling of Unused Pins in the manual.
- 2. Processing at Power-on

The state of the product is undefined at the moment when power is supplied.

- The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the moment when power is supplied.
 - In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the moment when power is supplied until the reset process is completed.

In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the moment when power is supplied until the power reaches the level at which resetting has been specified.

3. Prohibition of Access to Reserved Addresses

Access to reserved addresses is prohibited.

- The reserved addresses are provided for the possible future expansion of functions. Do
 not access these addresses; the correct operation of LSI is not guaranteed if they are
 accessed.
- 4. Clock Signals

After applying a reset, only release the reset line after the operating clock signal has become stable. When switching the clock signal during program execution, wait until the target clock signal has stabilized.

- When the clock signal is generated with an external resonator (or from an external oscillator) during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Moreover, when switching to a clock signal produced with an external resonator (or by an external oscillator) while program execution is in progress, wait until the target clock signal is stable.
- 5. Differences between Products

Before changing from one product to another, i.e. to one with a different part number, confirm that the change will not lead to problems.

— The characteristics of MPU/MCU in the same group but having different part numbers may differ because of the differences in internal memory capacity and layout pattern. When changing to products of different part numbers, implement a system-evaluation test for each of the products.

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